

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Claim 1. (Previously Presented): A method of generating ions, comprising:
heating an ion source material composed of indium iodide (InI) and having a particle size larger than 1 mm and not larger than 5 mm to generate a vapor of said indium iodide (InI); and
generating indium (In) ions by discharging said vapor.

Claims 2–4. (Canceled):

Claim 5. (Previously Presented): A method of irradiating ions, comprising:
heating an ion source material composed of indium iodide (InI) and having a particle size larger than 1 mm and not larger than 5 mm to generate a vapor of said indium iodide (InI);
generating indium (In) ions by discharging said vapor; and
selectively irradiating said indium (In) ions onto a substrate to be processed.

Claims 6–20. (Canceled):

Claim 21. (Previously Presented): The method according to claim 1, wherein said heating an ion source material comprises heating said indium iodide (InI) at a temperature of not lower than 275 °C and not higher than 380°C to generate said vapor of said indium iodide (InI).

Claims 22–28. (Canceled):

Claim 29. (Previously Presented): The method according to claim 1, wherein said heating an ion source material includes supplying said indium iodide into an oven which has an outlet nozzle for said vapor, followed by heating said indium iodide whose particle size is larger than a diameter of said outlet nozzle.

Claim 30. (Previously Presented): The method according to claim 1, wherein, in said step of generating indium (In) ions by discharging said vapor, a support gas inlet to an arc chamber and a vapor inlet to said arc chamber are provided on one face of said arc chamber, and are configured to introduce support gas and said vapor into said arc chamber.

Claim 31. (Previously Presented): A method of generating ions, comprising:
heating an ion source material composed of indium iodide (InI) which is supplied in an oven having a vapor outlet nozzle and whose particle size is larger than a diameter of said outlet nozzle; and
generating indium (In) ions by discharging said vapor.

Claim 32. (Previously Presented): The method according to claim 31, wherein said heating an ion source material includes heating said indium iodide at a temperature of not lower than 275°C and not higher than 380°C.

Claim 33. (Previously Presented): The method according to claim 31, wherein, in said step of generating indium (In) ions by discharging said vapor, a support gas inlet to an arc chamber and a vapor inlet to said arc chamber are provided on one face of said arc chamber, and are configured to introduce support gas and said vapor generated into said arc chamber.

Claim 34. (Currently Amended): A method of irradiating ions, comprising:
heating an ion source material to generate vapor thereof, the ion source material being composed of indium iodide (InI) which is supplied in an oven having a vapor outlet nozzle and whose particle size is larger than a diameter of said outlet nozzle;
generating indium (In) ions by discharging said vapor; and
selectively irradiating said indium (In) ions onto a substrate to be processed.

Claims 35–37. (Cancelled):

Claim 38. (New): The method according to claim 5, wherein said heating an ion source material includes supplying said indium iodide into an oven which has an outlet nozzle for said vapor, followed by heating said indium iodide whose particle size is larger than a diameter of said outlet nozzle.

Claim 39. (New): The method according to claim 34, wherein the ion source material composed of indium iodide has a particle size larger than 1 mm and not larger than 5 mm.